

FIG. 1

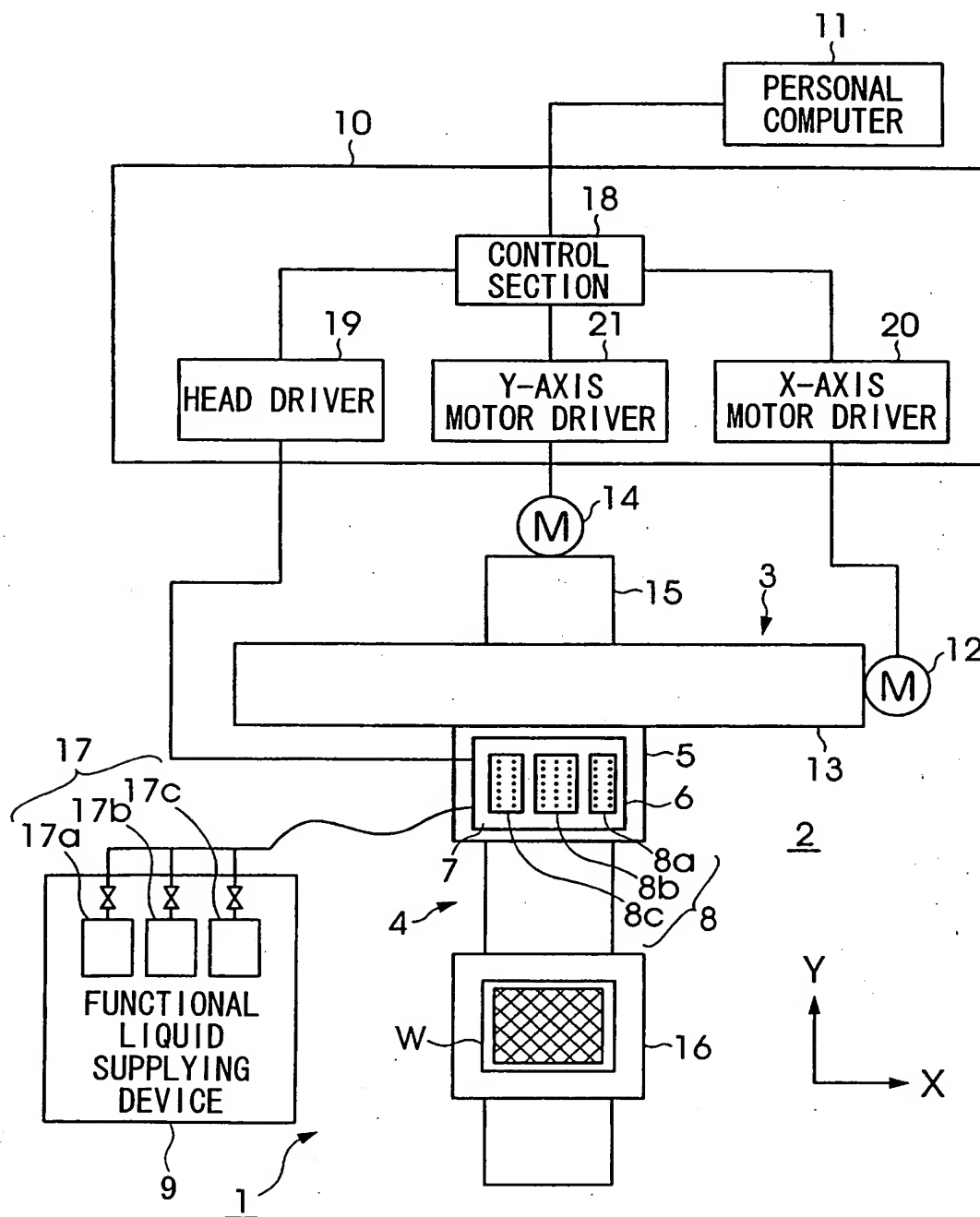


FIG. 2

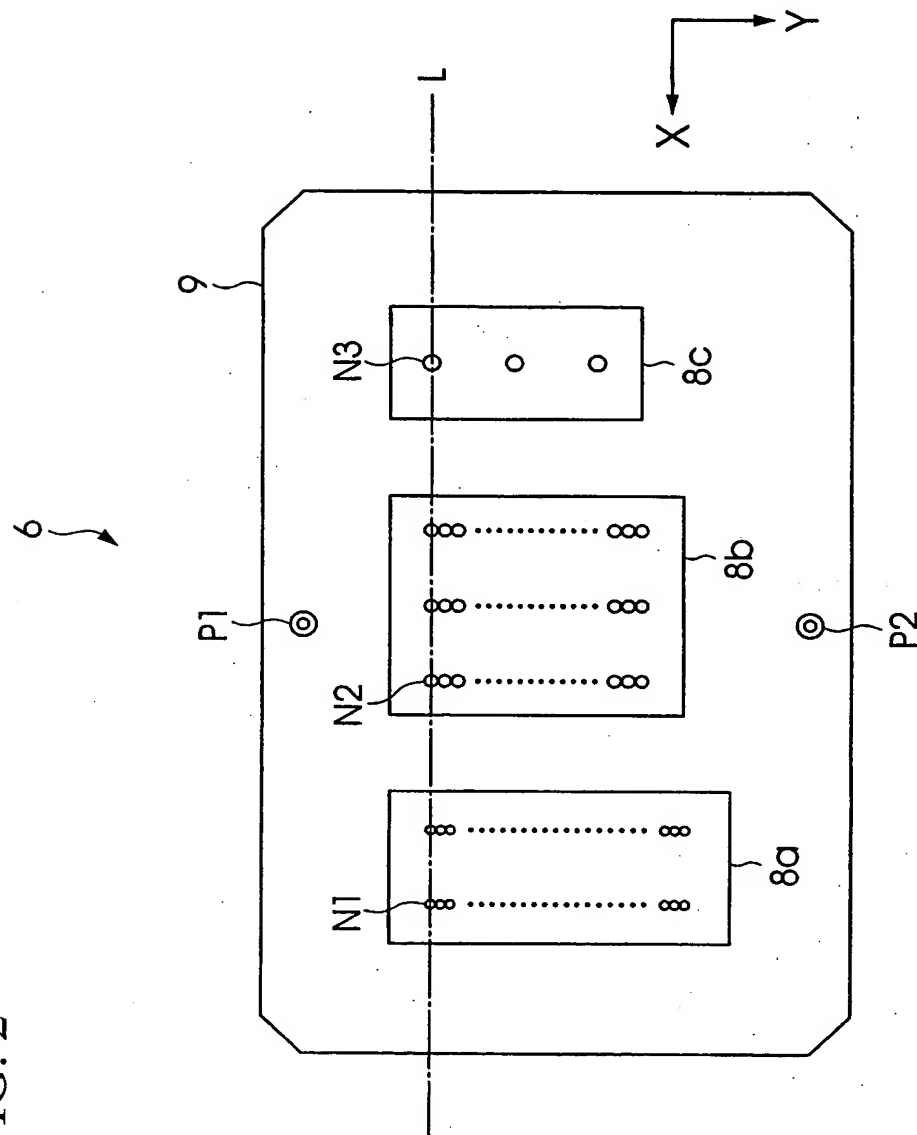


FIG. 3

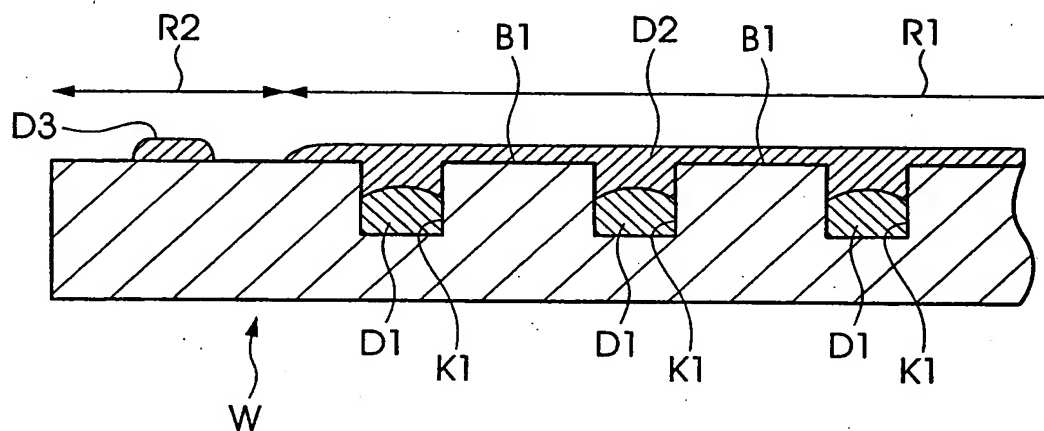


FIG. 4

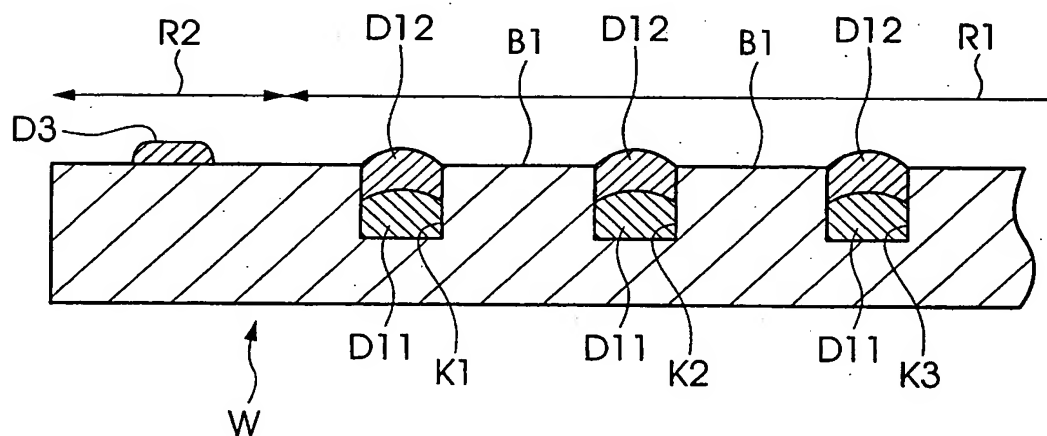


FIG. 5

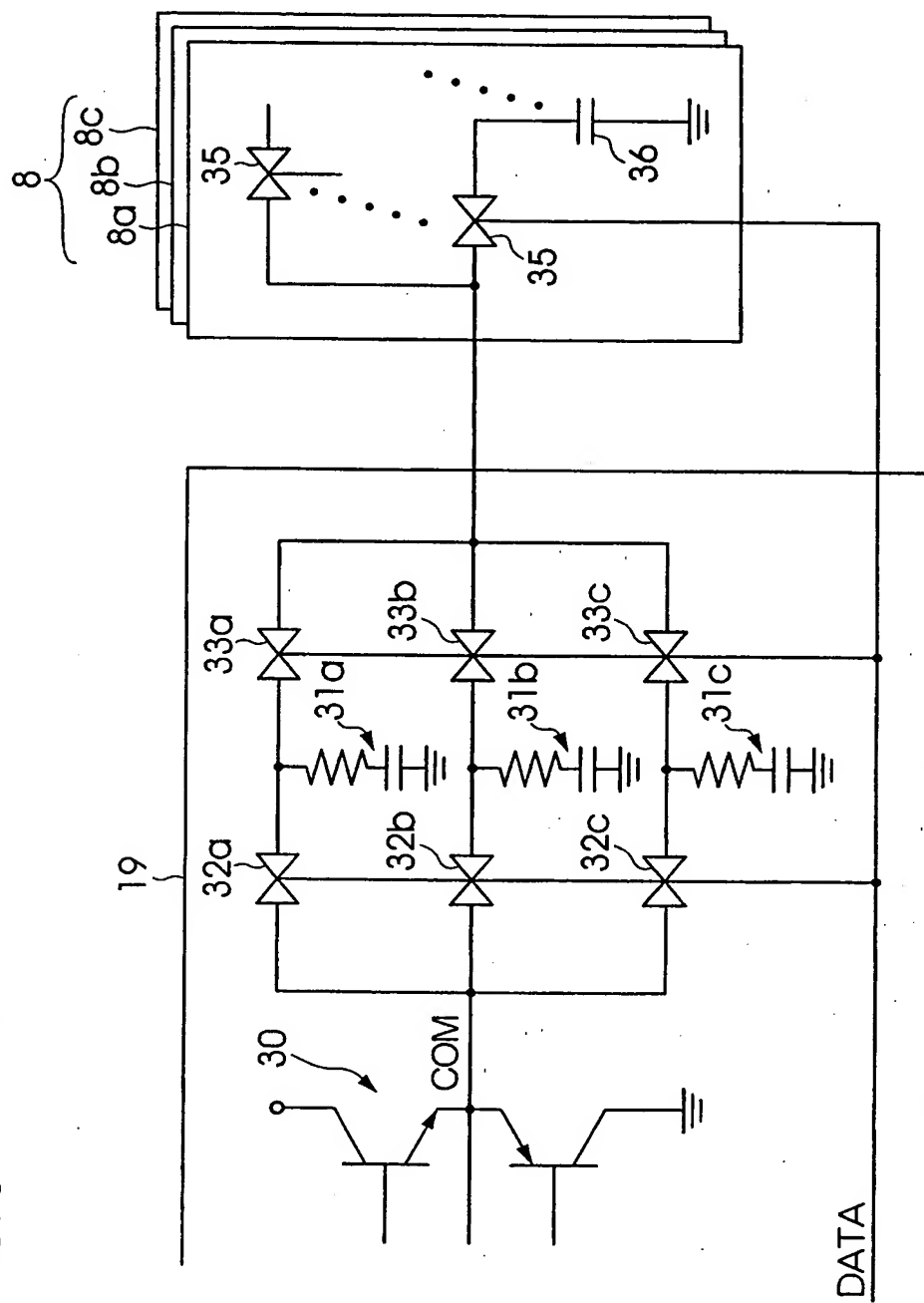


FIG. 6

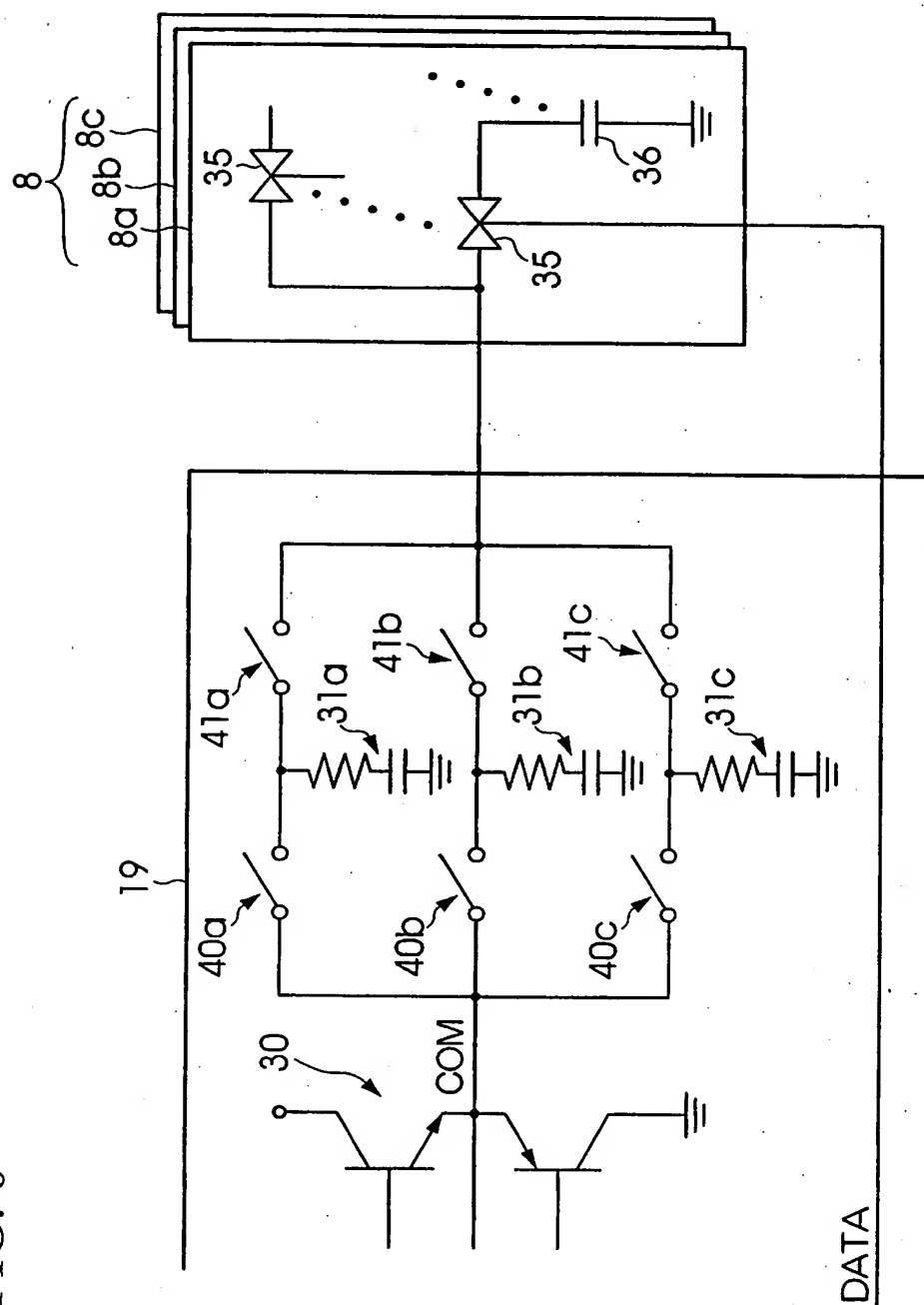


FIG. 7

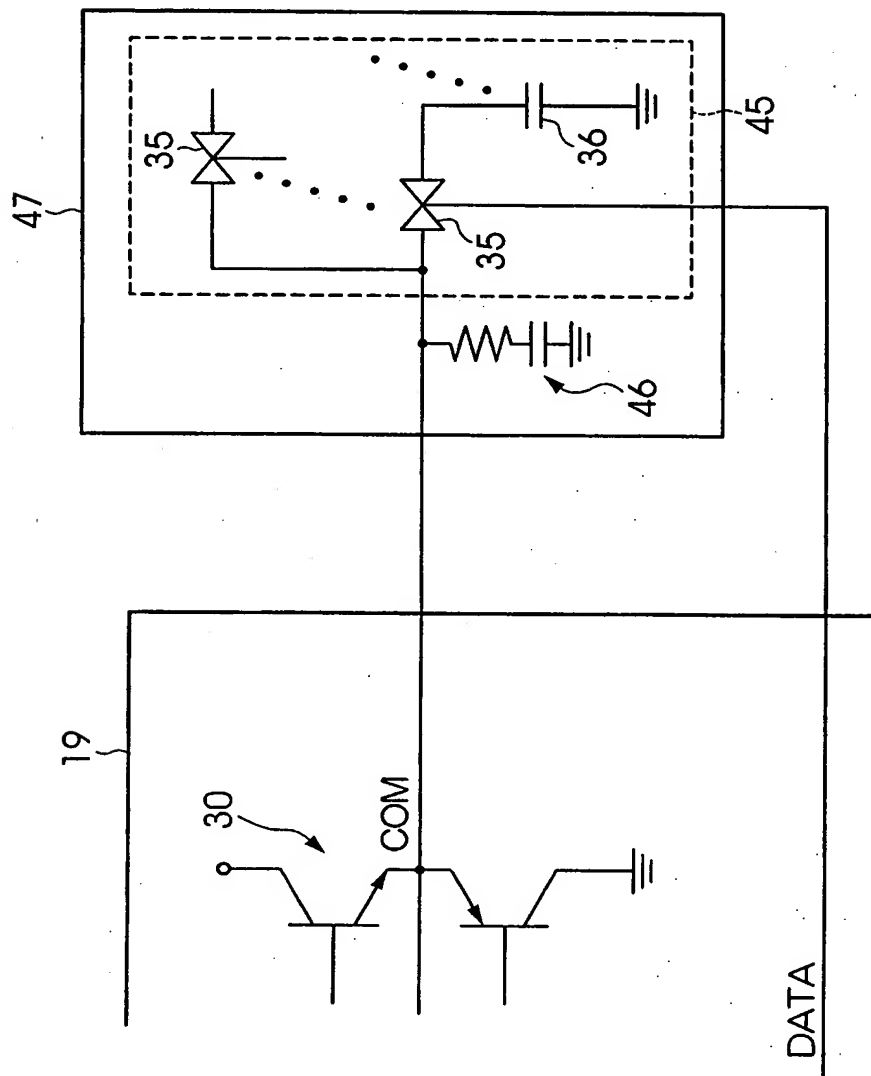


FIG. 8

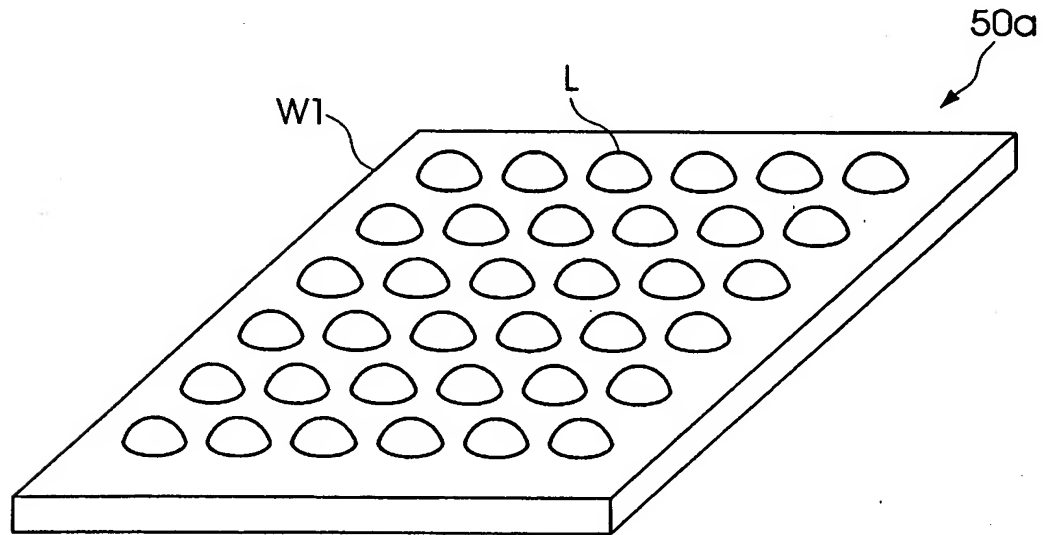


FIG. 9

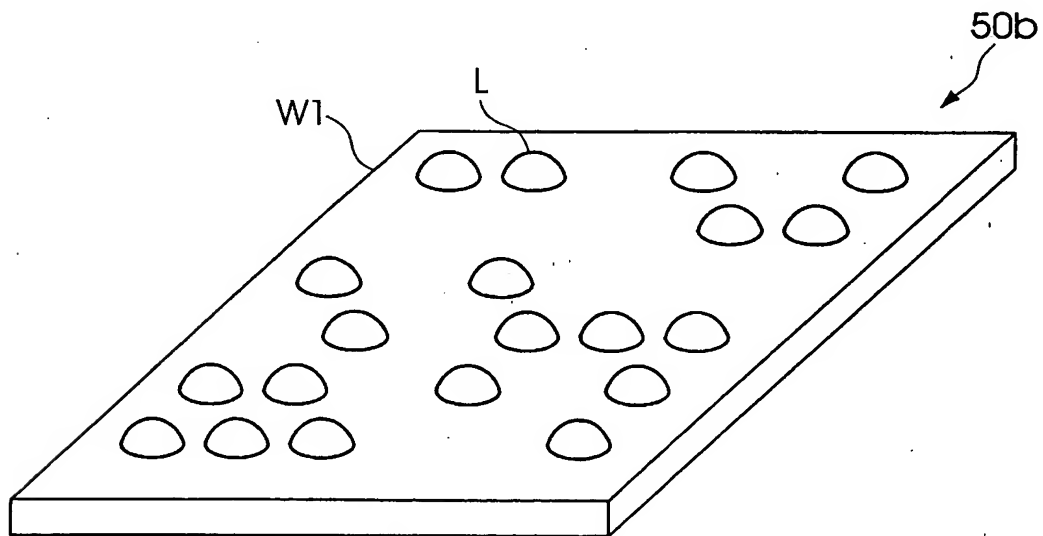


FIG. 10

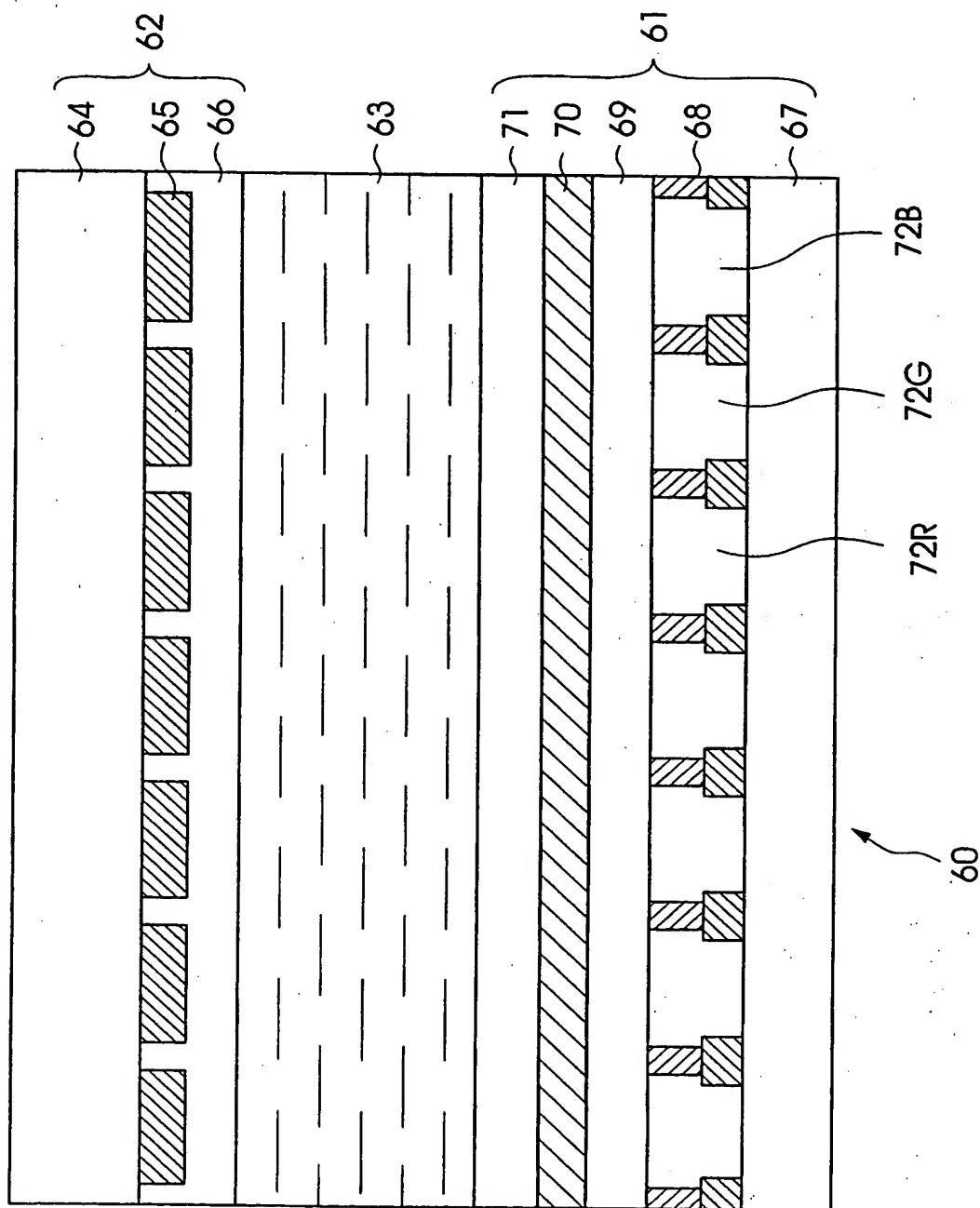




FIG. 11A

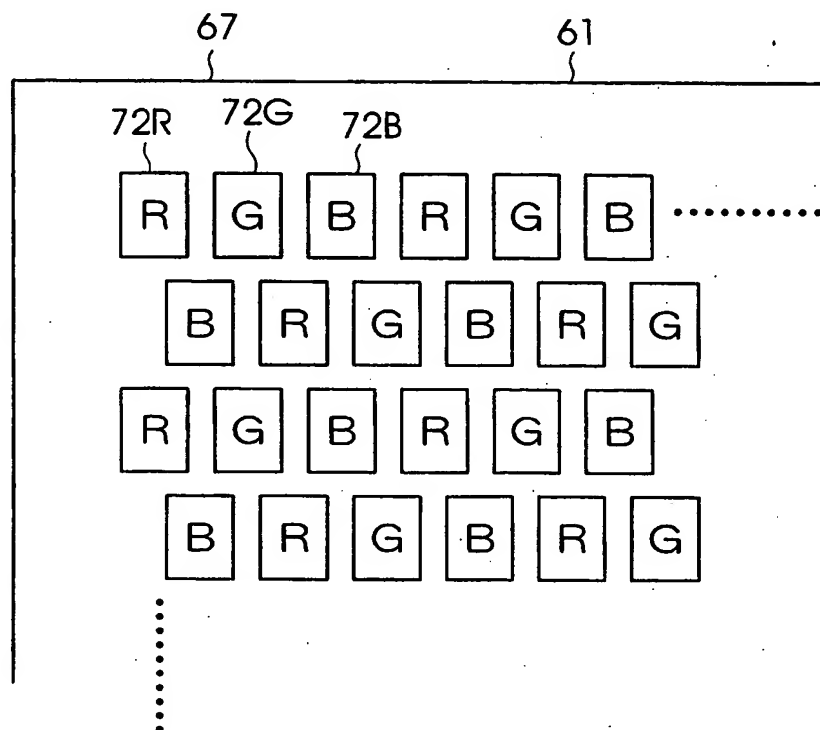
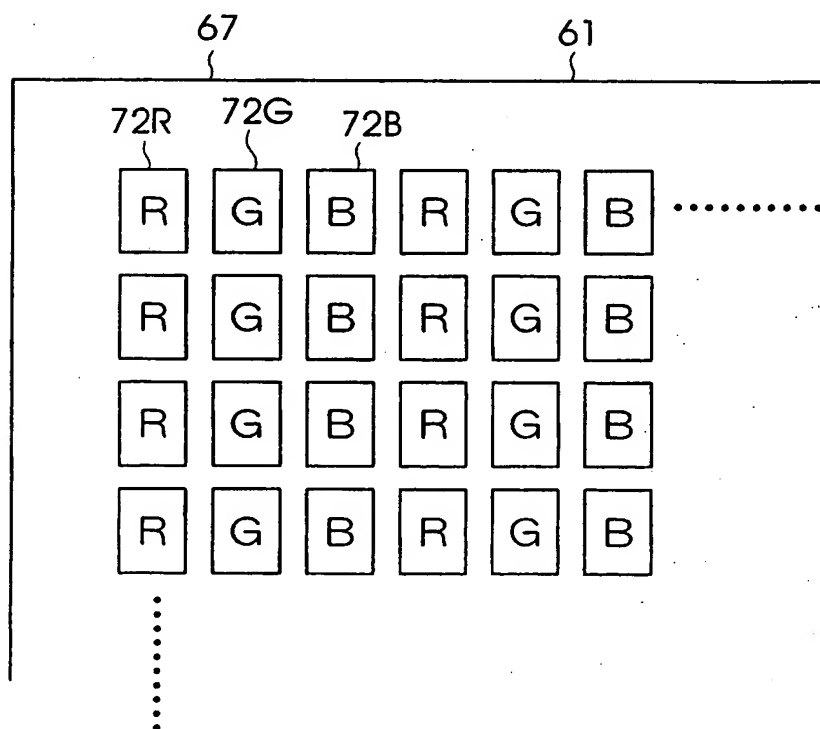


FIG. 11B



This cross-sectional view shows a semiconductor device with a substrate 301. A top layer 371 is positioned above a series of repeating structures. Each structure includes a layer 344, a layer 351, and a layer 352. A layer 353 is also present, with a bracket indicating it is part of a group with 352. A layer 361 is located at the bottom of the repeating structures. The device is divided into three main regions: 302, 321, and 311. The regions 302 and 321 are separated by a vertical line, and the region 311 is separated by another vertical line. The regions 302 and 321 are filled with a material having diagonal hatching, while the region 311 is filled with a material having a different hatching pattern.

FIG. 13

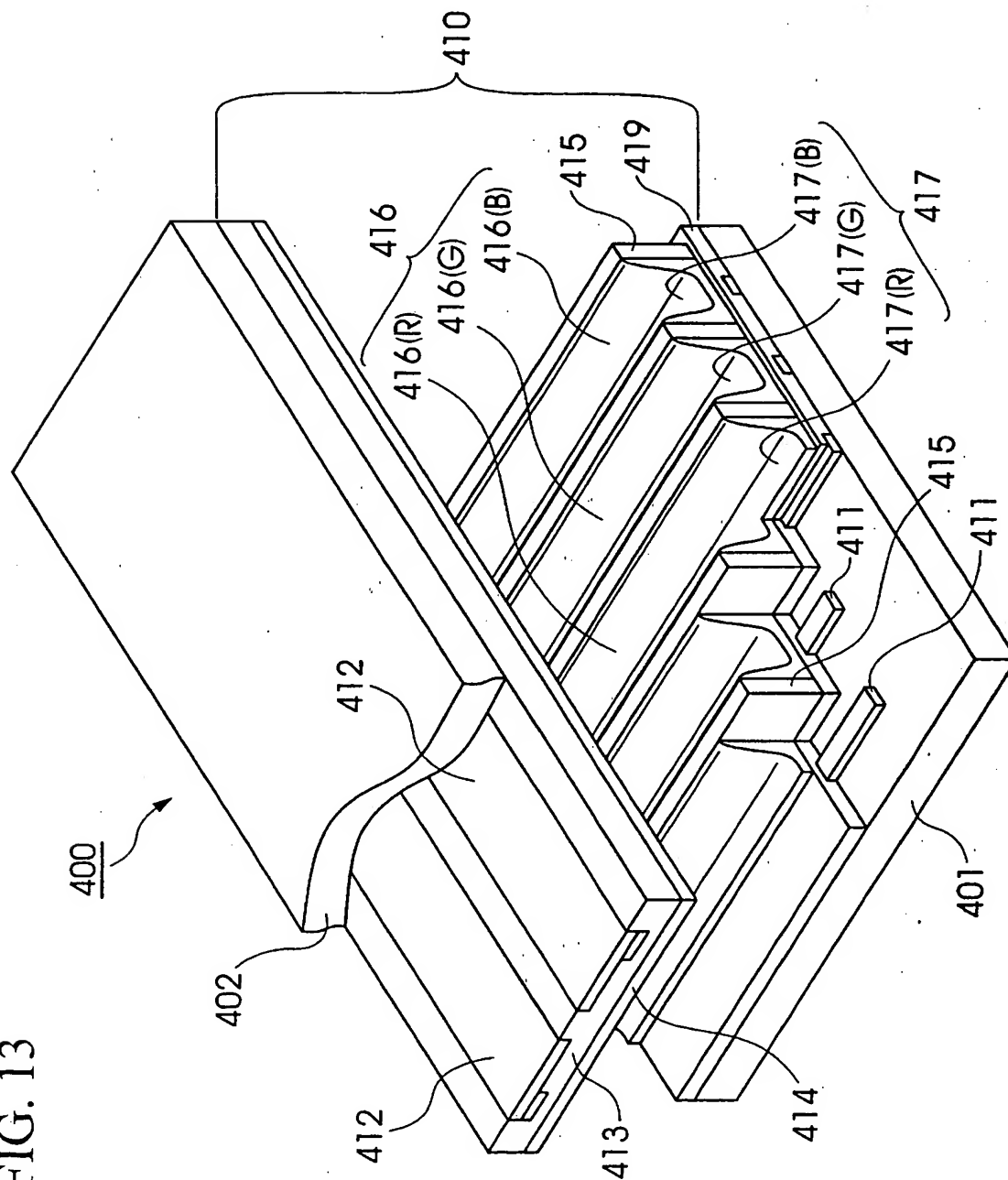


FIG. 14A

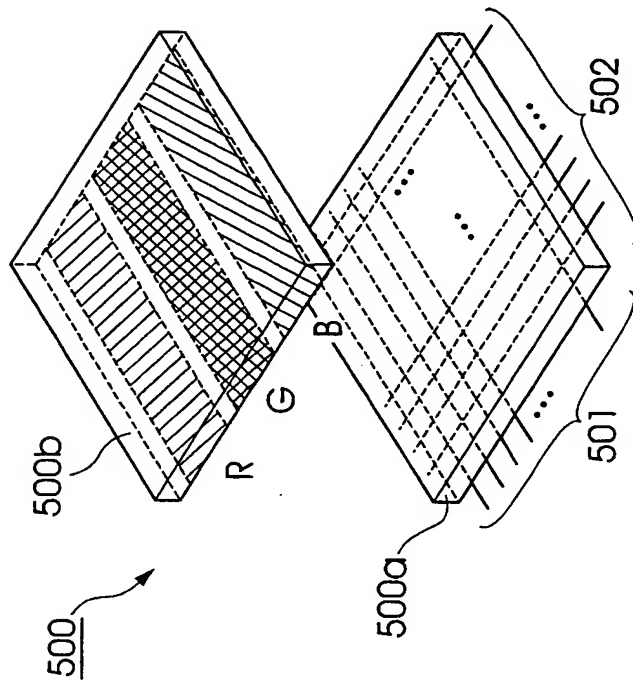


FIG. 14B

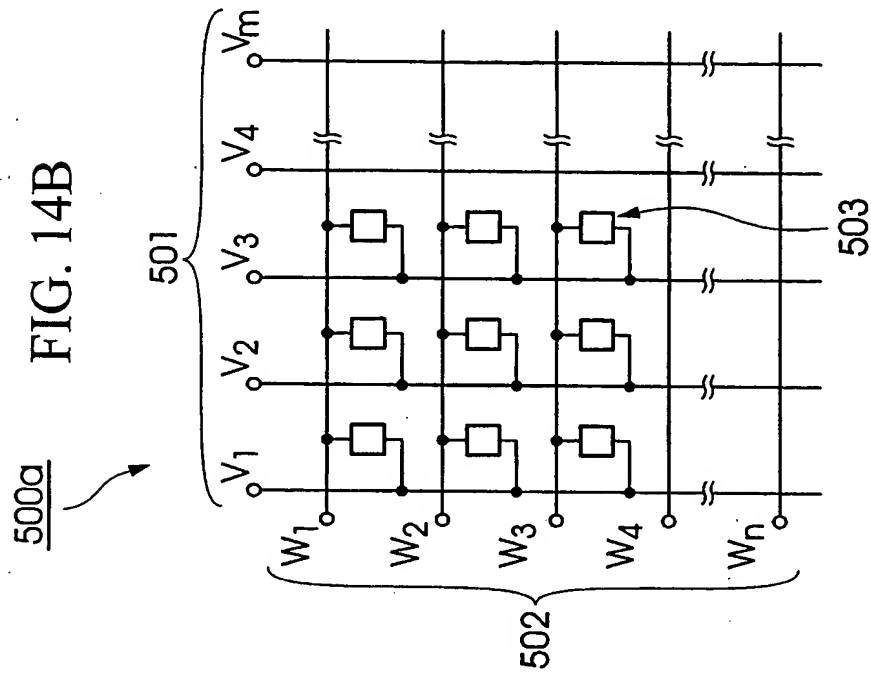


FIG. 14C

